

Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
Channel 1	30	0.0145 at V _{GS} = 10 V	10.8	8.3
		0.0195 at V _{GS} = 4.5 V	9.3	
Channel 2	30	0.0265 at V _{GS} = 10 V	7.2	4
		0.036 at V _{GS} = 4.5 V	6.2	

FEATURES

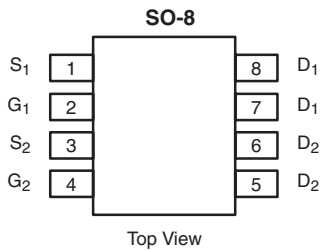
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 % R_g Tested



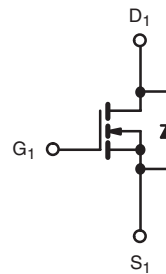
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

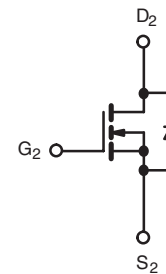
- Logic DC/DC for Notebook PC



Ordering Information: Si4972DY-T1-E3 (Lead (Pb)-free)
Si4972DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted					
Parameter		Symbol	Channel 1	Channel 2	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	10.8	7.2	A
	$T_C = 70\text{ }^{\circ}\text{C}$		8.7	5.7	
	$T_A = 25\text{ }^{\circ}\text{C}$		8.7 ^{b,c}	6.4 ^{b,c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		6.9 ^{b,c}	5.1 ^{b,c}	
Pulsed Drain Current (10 μ s Pulse Width)		I_{DM}	20	20	
Source-Drain Current Diode Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_S	2.5	2.1	
	$T_A = 25\text{ }^{\circ}\text{C}$		1.6 ^{b,c}	1.6 ^{b,c}	
Pulsed Source-Drain Current		I_{SM}	20	20	
Single Pulse Avalanche Current	$L = 0.1\text{ mH}$	I_{AS}	15	6	mJ
Avalanche Energy		E_{AS}	11	1.8	
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	3.1	2.5	W
	$T_C = 70\text{ }^{\circ}\text{C}$		2.1	1.6	
	$T_A = 25\text{ }^{\circ}\text{C}$		2.0 ^{b,c}	2.0 ^{b,c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.25 ^{b,c}	1.25 ^{b,c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Channel 1		Channel 2	
			Typical	Maximum	Typical	Maximum
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	52	62.5	55	62.5
Maximum Junction-to-Foot (Drain)	Steady	R _{thJF}	32	40	40	50

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 110 °C/W (Ch 1) and 120 °C/W (Ch 2).

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch 1	30			V	
		V _{GS} = 0 V, I _D = 250 μA	Ch 2	30				
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	Ch 1		35		mV/°C	
		I _D = 250 μA	Ch 2		35			
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	Ch 1		- 6.5			
		I _D = 250 μA	Ch 2		- 6.5			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch 1	1.5		3.0	V	
		V _{DS} = V _{GS} , I _D = 250 μA	Ch 2	1.5		3.0		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	Ch 1 Ch 2			100 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch 1			1	μA	
		V _{DS} = 30 V, V _{GS} = 0 V	Ch 2			1		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch 1			10		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch 2			10		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch 1	10			A	
		V _{DS} = 5 V, V _{GS} = 10 V	Ch 2	10				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 6 A	Ch 1		0.012	0.0145	Ω	
		V _{GS} = 10 V, I _D = 4.5 A	Ch 2		0.022	0.0265		
		V _{GS} = 4.5 V, I _D = 5.6 A	Ch 1		0.016	0.0195		
		V _{GS} = 4.5 V, I _D = 4 A	Ch 2		0.030	0.036		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 6 A	Ch 1		27		S	
		V _{DS} = 15 V, I _D = 4.5 A	Ch 2		20			
Dynamic ^a								
Input Capacitance	C _{iss}	Channel 1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch 1 Ch 2		1080 515		pF	
Output Capacitance	C _{oss}		Ch 1 Ch 2		170 91			
Reverse Transfer Capacitance	C _{rss}		Channel 2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch 1 Ch 2		72 38		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 5 A	Ch 1 Ch 2		18.5 9.6	28 15	nC	
		Channel 1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5 A	Ch 1 Ch 2		8.3 4	13 6		
			Channel 2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5 A	Ch 1 Ch 2		3.9 1.9		
					Ch 1 Ch 2			2.7 1.3
Gate-Source Charge	Q _{gs}							
Gate-Drain Charge	Q _{gd}							
Gate Resistance	R _g	f = 1 MHz	Ch 1 Ch 2		2.5 2.9	3.8 4.4		Ω



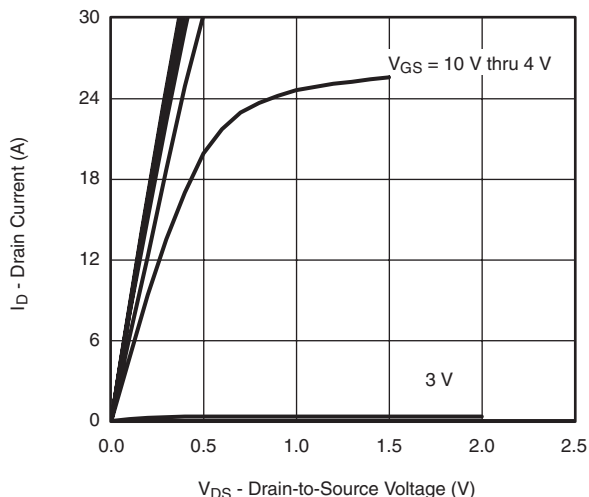
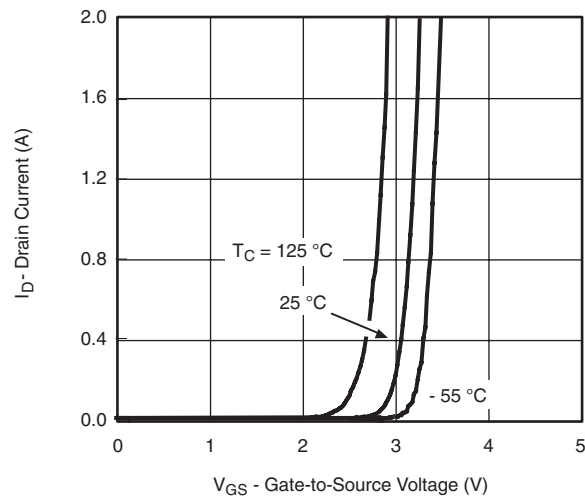
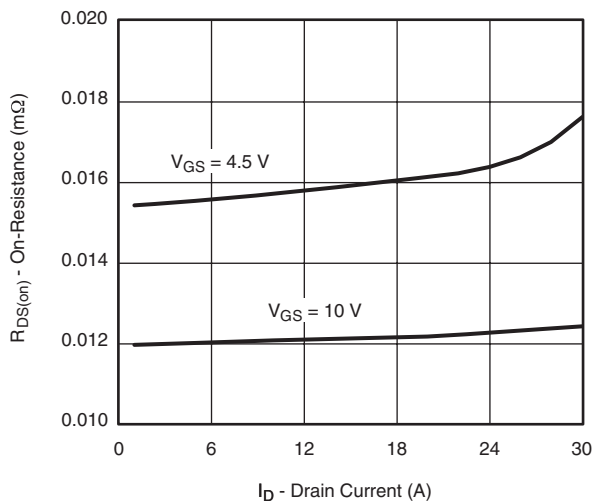
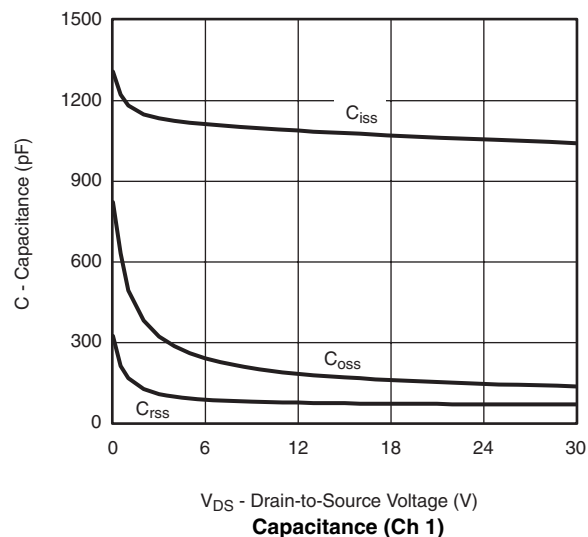
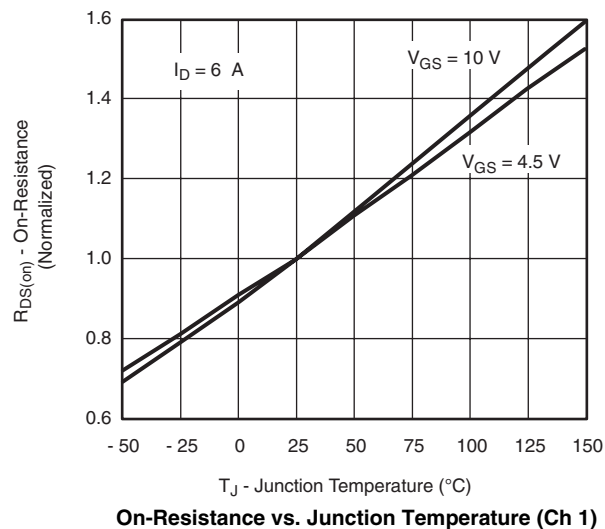
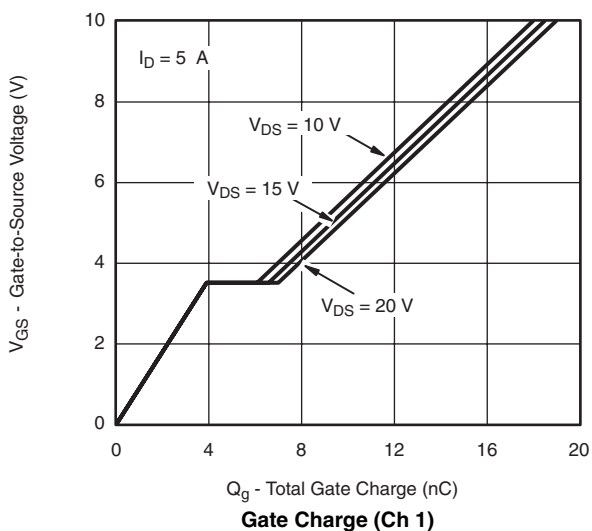
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Dynamic ^a							
Turn-On Delay Time	$t_{d(on)}$	Channel 1 $V_{DD} = 15\text{ V}$, $R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	Ch 1		12	18	ns
			Ch 2		10	15	
Rise Time	t_r		Ch 1		55	83	
			Ch 2		60	90	
Turn-Off DelayTime	$t_{d(off)}$	Ch 1		30	45		
		Ch 2		22	33		
Fall Time	t_f	Ch 1		7	11		
		Ch 2		6	9		
Turn-On Delay Time	$t_{d(on)}$	Channel 1 $V_{DD} = 15\text{ V}$, $R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$	Ch 1		120	180	
			Ch 2		108	162	
Rise Time	t_r		Ch 1		150	225	
			Ch 2		130	195	
Turn-Off Delay Time	$t_{d(off)}$	Ch 1		29	44		
		Ch 2		19	29		
Fall Time	t_f	Ch 1		13	20		
		Ch 2		26	39		
Drain-Source Body Diode Characteristics							
Continous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$	Ch 1			2.5	A
			Ch 2			2.1	
Pulse Diode Forward Current ^a	I_{SM}		Ch 1			20	
			Ch 2			20	
Body Diode Voltage	V_{SD}	$I_S = 1.6\text{ A}$	Ch 1		0.77	1.2	V
		$I_S = 1.6\text{ A}$	Ch 2		0.79	1.2	
Body Diode Reverse Recovery Time	t_{rr}	Channel 1 $I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	Ch 1		21	42	ns
			Ch 2		18	36	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch 1		15	30	nC
			Ch 2		11	22	
Reverse Recovery Fall Time	t_a	Channel 2 $I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	Ch 1		13		ns
			Ch 2		11		
Reverse Recovery Rise Time	t_b		Ch 1		8		
			Ch 2		7		

Notes:

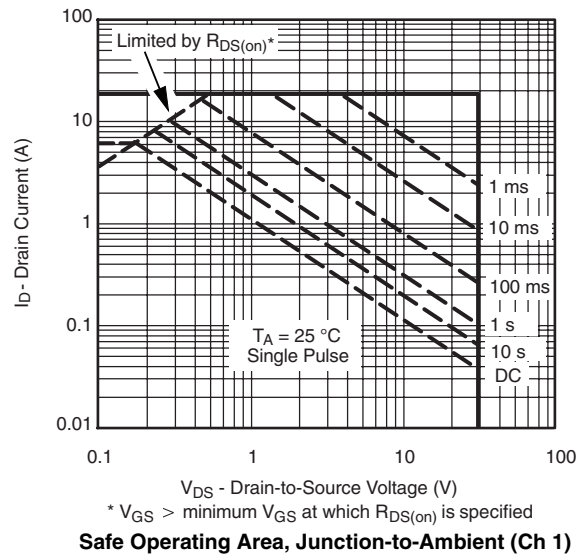
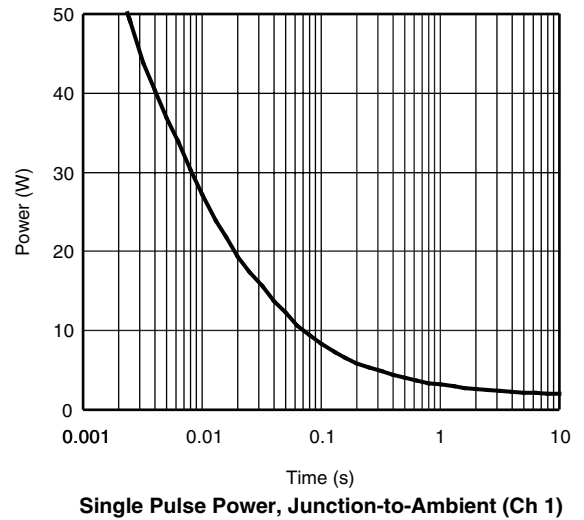
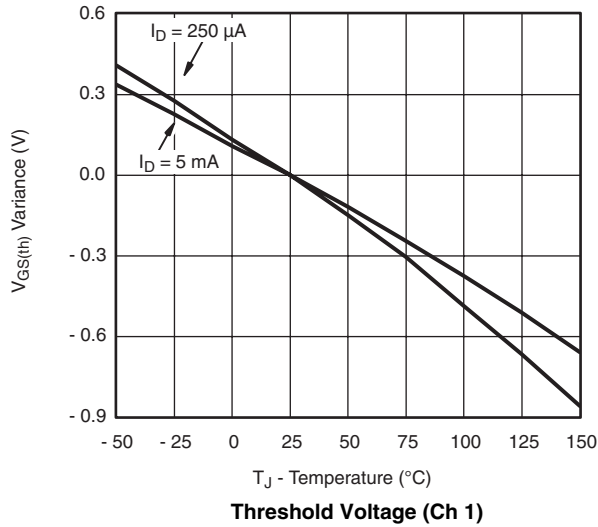
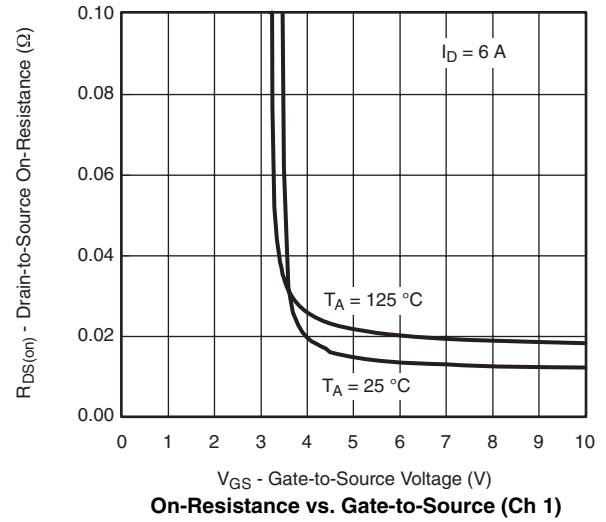
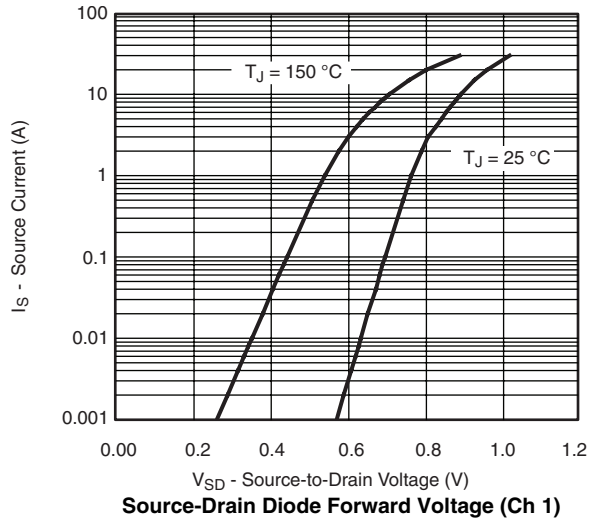
a. Guaranteed by design, not subject to production testing.

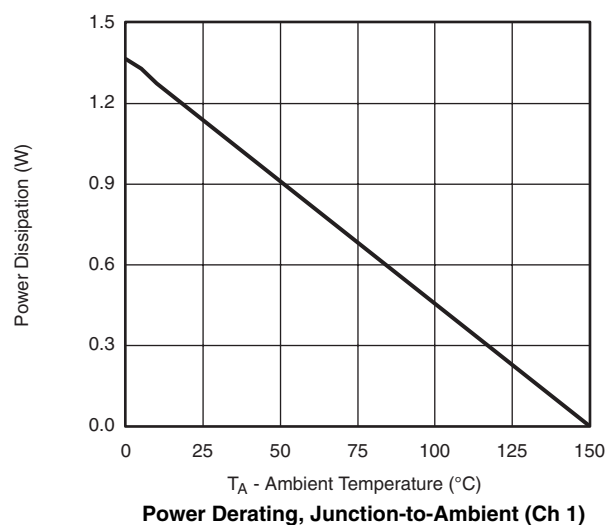
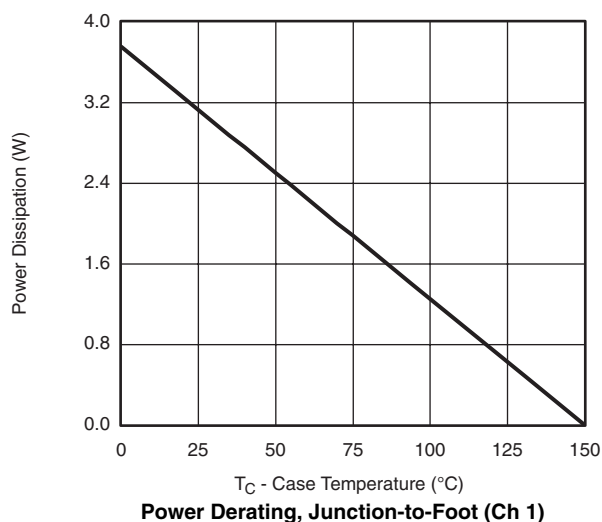
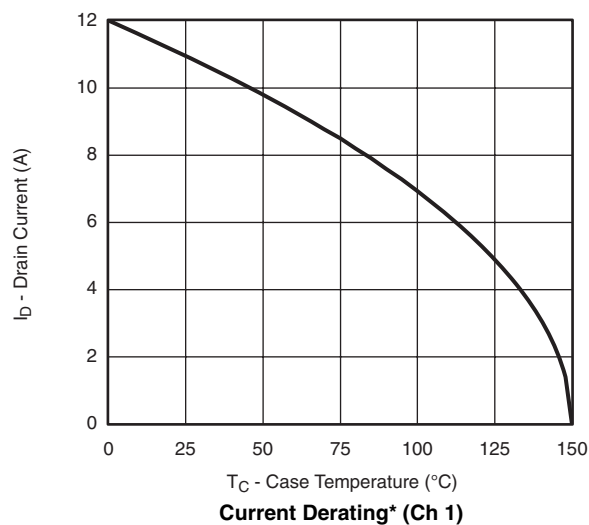
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics (Ch 1)****Transfer Characteristics (Ch 1)****On-Resistance vs. Drain Current and Gate Voltage (Ch 1)****Capacitance (Ch 1)**

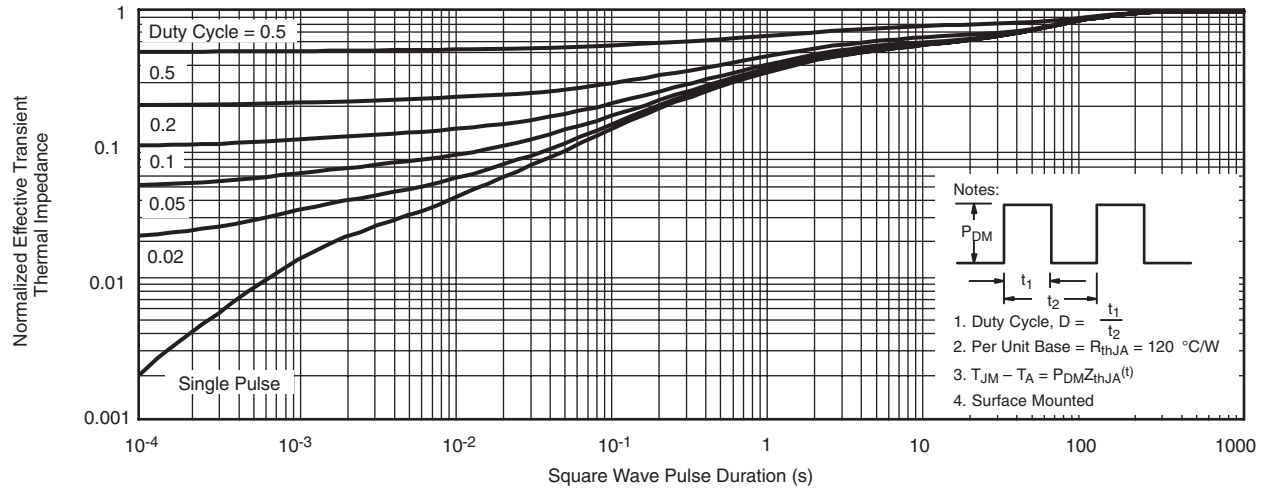
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



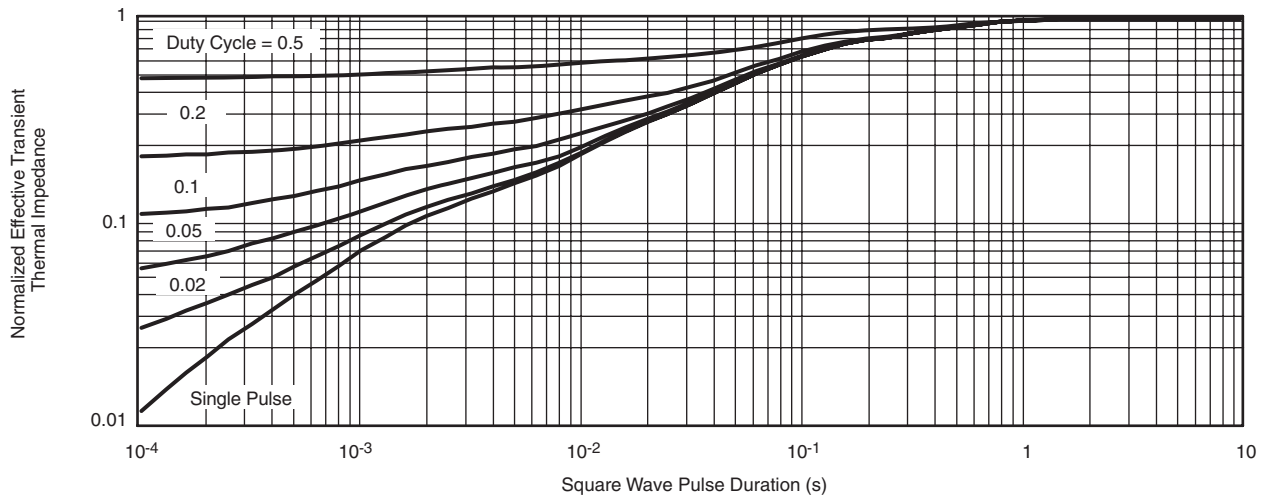
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

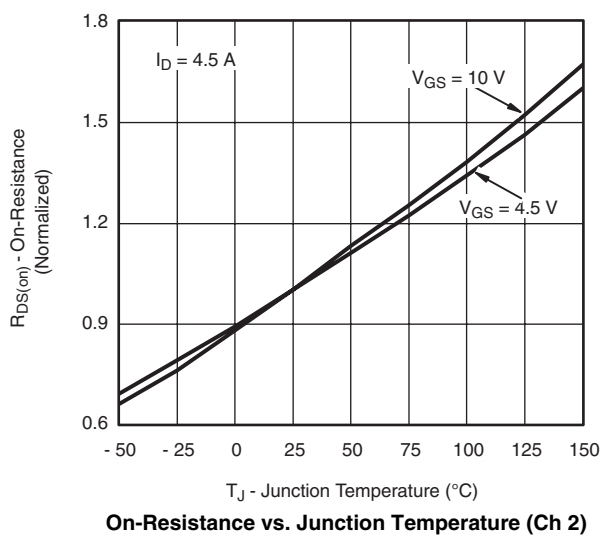
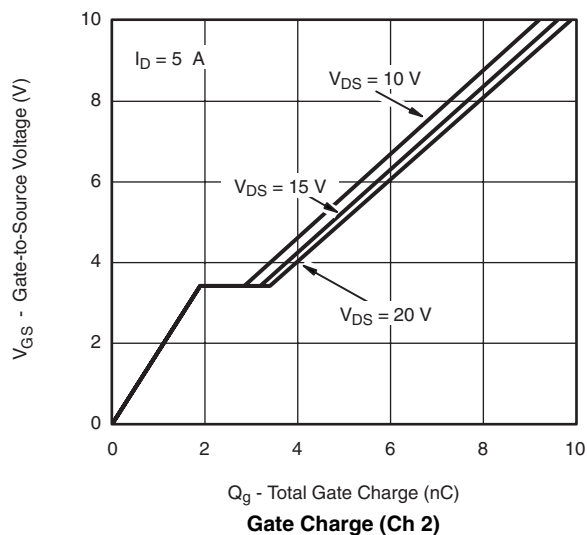
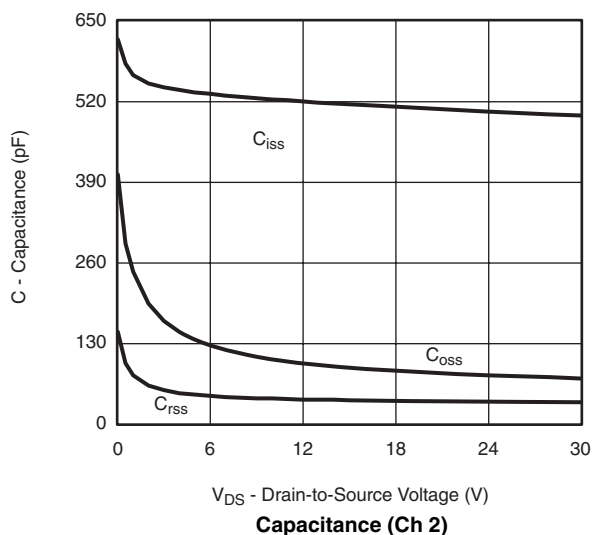
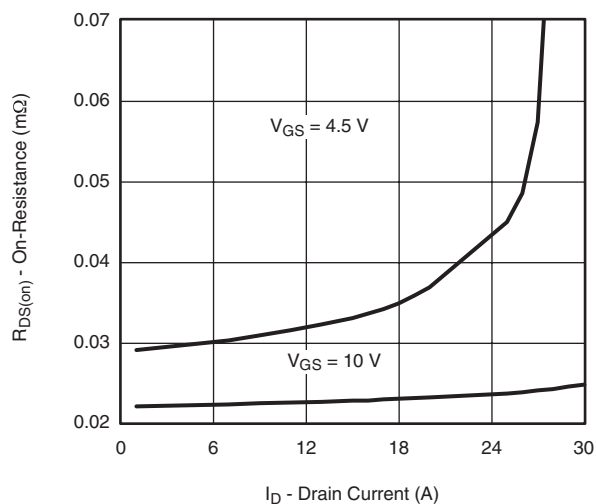
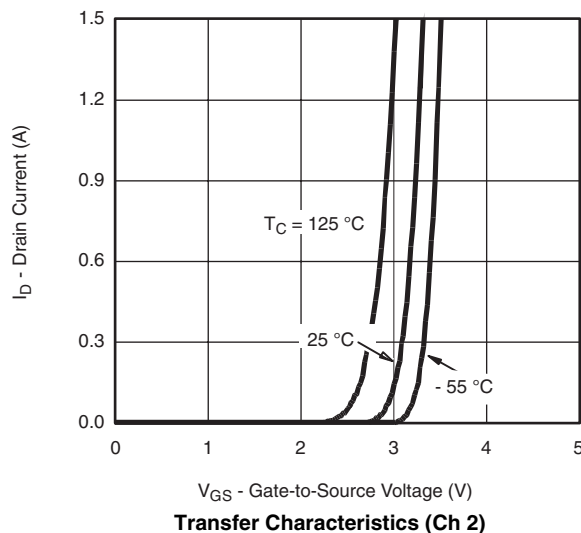
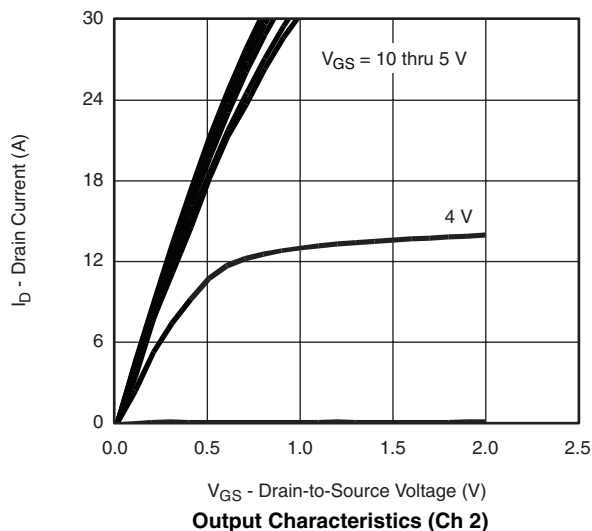
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



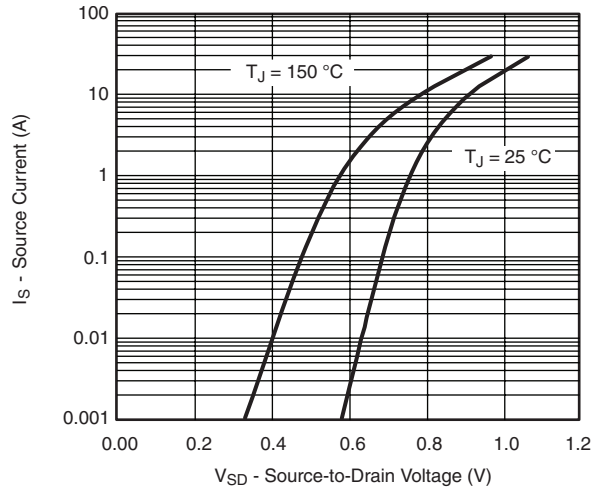
Normalized Thermal Transient Impedance, Junction-to-Ambient (Ch 1)



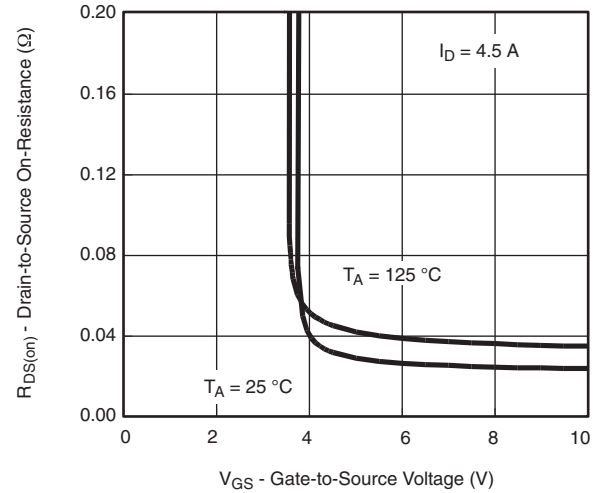
Normalized Thermal Transient Impedance, Junction-to-Case (Ch 1)

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

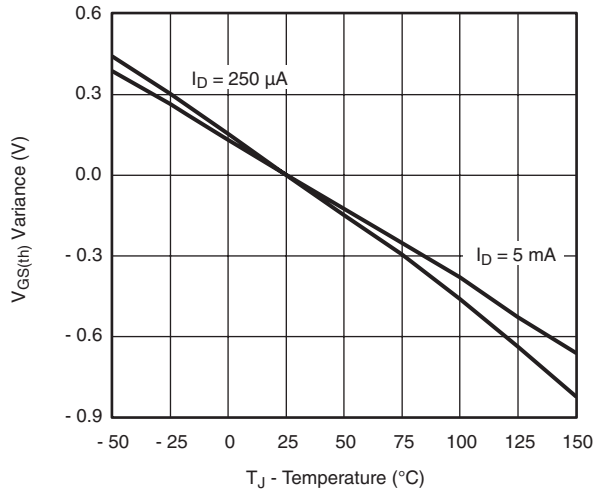
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



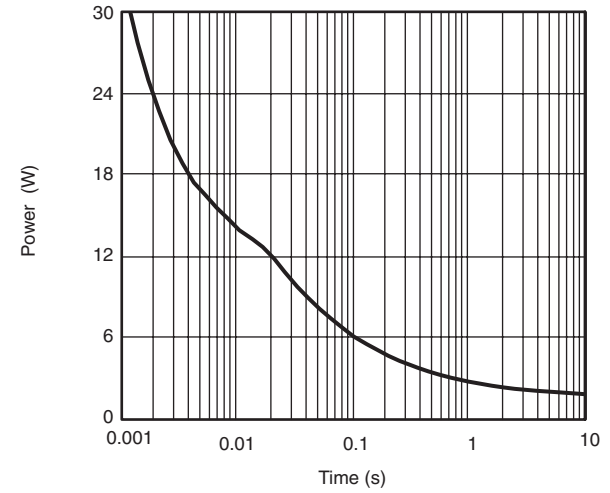
Source-Drain Diode Forward Voltage (Ch 2)



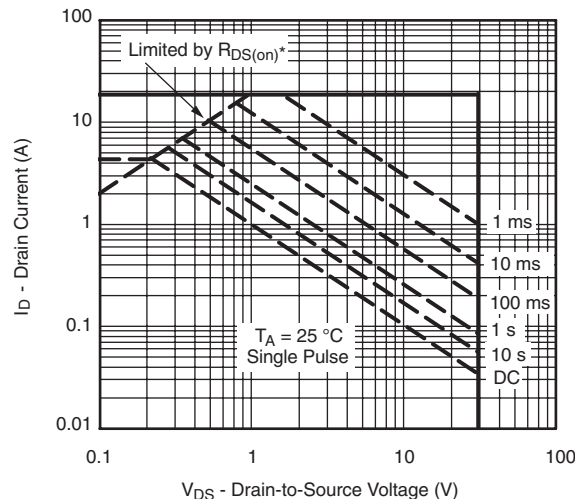
On-Resistance vs. Gate-to-Source Temperature (Ch 2)



Threshold Voltage (Ch 2)

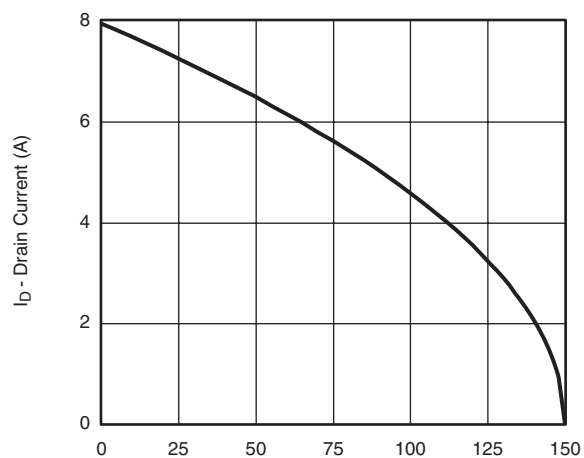
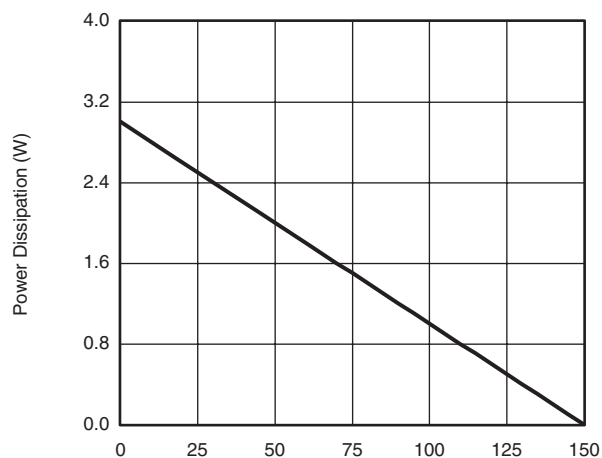
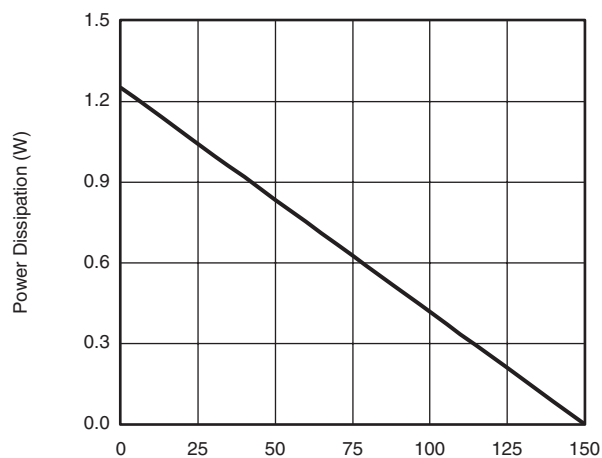


Single Pulse Power, Junction-to-Ambient (Ch 2)



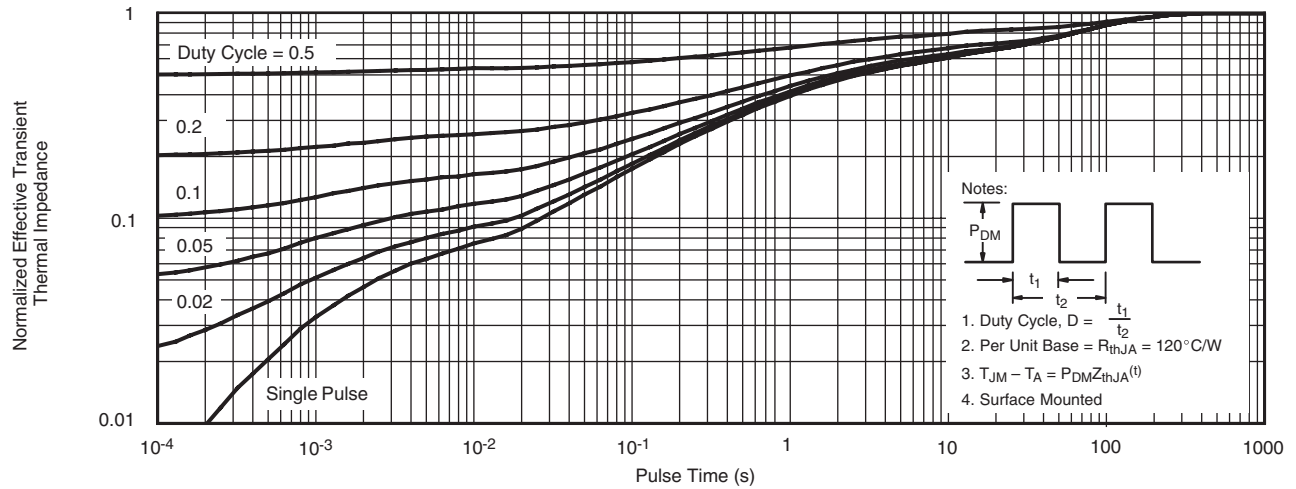
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient (Ch 2)

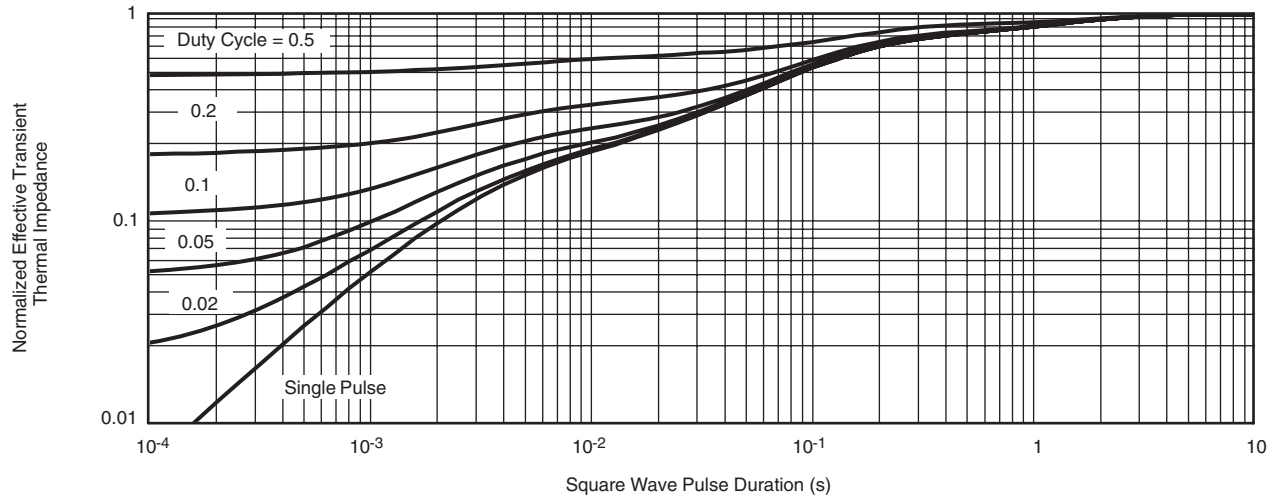
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted T_C - Case Temperature (°C)**Current Derating* (Ch 2)** T_C - Case Temperature (°C)**Power Derating, Junction-to-Foot (Ch 2)** T_A - Ambient Temperature (°C)**Power Derating, Junction-to-Ambient (Ch 2)**

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient (Ch 2)



Normalized Thermal Transient Impedance, Junction-to-Case (Ch 2)

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